



# PSMN041-100MSE

N-channel 100 V 42 mOhm standard level ASFET with enhanced SOA in LFAK33 package. Designed specifically for high power PoE applications

3 May 2022

Objective data sheet

## 1. General description

New standards and proprietary approaches are enabling Power-over-Ethernet (PoE) systems capable of delivering up to 90 W to each powered device (PD). Such solutions place increased demands on the power sourcing equipment (PSE) in terms of “soft-start”, thermal management and power density requirements.

## 2. Features and benefits

- Enhanced safe operating area (SOA) for superior linear mode operation
- Low  $R_{DSon}$  for low  $I^2R$  losses
- Ultra reliable LFAK33 package for superior thermal and ruggedness performance
- Very low  $I_{DSS}$  leakage

## 3. Applications

- High power PoE applications (>50 W)
- IEEE802.3at and proprietary solutions
- CCTV
- WiFi hotspots
- 5G picocells
- Fault tolerant load switch - Inrush management and eFuse applications

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	100	V
$I_D$	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$	-	-	25	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	59	W
$T_j$	junction temperature		-55	-	175	°C
<b>Static characteristics</b>						
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 25\text{ °C}$	-	32	42	mΩ
		$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; T_j = 100\text{ °C}$	-	50	67	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$I_D = 25\text{ A}; V_{DS} = 50\text{ V}; V_{GS} = 10\text{ V}; T_j = 25\text{ °C}$	[tbd]	2	[tbd]	nC
$Q_{G(tot)}$	total gate charge		[tbd]	10.5	[tbd]	nC
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 13\text{ A}; V_{sup} \leq 100\text{ V}; R_{GS} = 50\text{ }\Omega; V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; \text{unclamped}; t_p = 22\text{ s}$	[1]	-	18.5	mJ

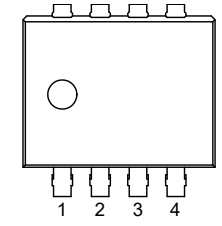
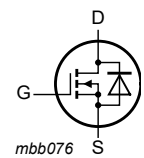
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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Source-drain diode</b>						
$Q_r$	recovered charge	$I_S = 25 \text{ A}$ ; $di_S/dt = -100 \text{ A}/\mu\text{s}$ ; $V_{GS} = 0 \text{ V}$ ; $V_{DS} = 50 \text{ V}$ ; $T_j = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 5</a>	-	22	-	nC

[1] Protected by 100% test

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN041-100MSE	LPAK33	Plastic, single ended surface mounted package (LPAK33); 8 leads; 0.65 mm pitch	SOT1210

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$	-	100	V
$V_{DGR}$	drain-gate voltage	$25 \text{ }^\circ\text{C} \leq T_j \leq 175 \text{ }^\circ\text{C}$ ; $R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-20	20	V
$P_{tot}$	total power dissipation	$T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a>	-	59	W
$I_D$	drain current	$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	25	A
		$V_{GS} = 10 \text{ V}$ ; $T_{mb} = 100 \text{ }^\circ\text{C}$	-	18	A
$I_{DM}$	peak drain current	pulsed; $t_p \leq 10 \text{ }\mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$ ; <a href="#">Fig. 2</a>	-	100	A
$T_{stg}$	storage temperature		-55	175	$^\circ\text{C}$
$T_j$	junction temperature		-55	175	$^\circ\text{C}$
$T_{sld(M)}$	peak soldering temperature		-	260	$^\circ\text{C}$
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	25	A
$I_{SM}$	peak source current	pulsed; $t_p \leq 10 \text{ }\mu\text{s}$ ; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	100	A

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Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Avalanche ruggedness</b>						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 13 \text{ A}$ ; $V_{sup} \leq 100 \text{ V}$ ; $R_{GS} = 50 \Omega$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; unclamped; $t_p = 22 \text{ s}$	[1]	-	18.5	mJ
$I_{AS}$	non-repetitive avalanche current	$V_{sup} = 100 \text{ V}$ ; $V_{GS} = 10 \text{ V}$ ; $T_{j(\text{init})} = 25 \text{ }^\circ\text{C}$ ; $R_{GS} = 50 \Omega$	[1]	-	13	A

[1] Protected by 100% test

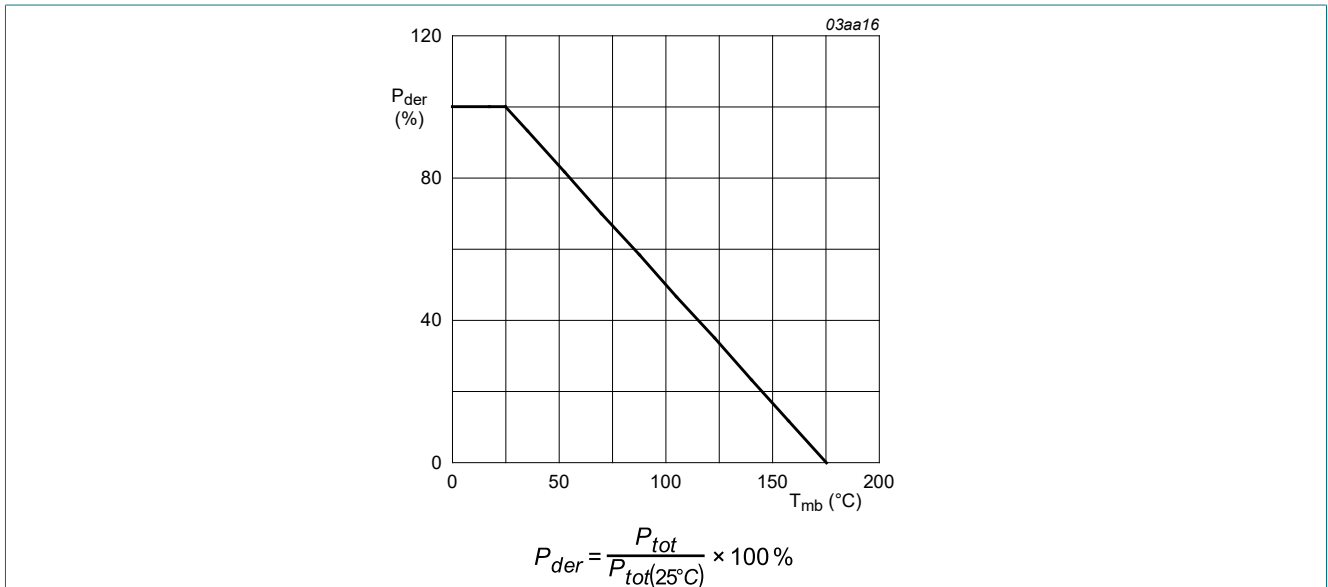
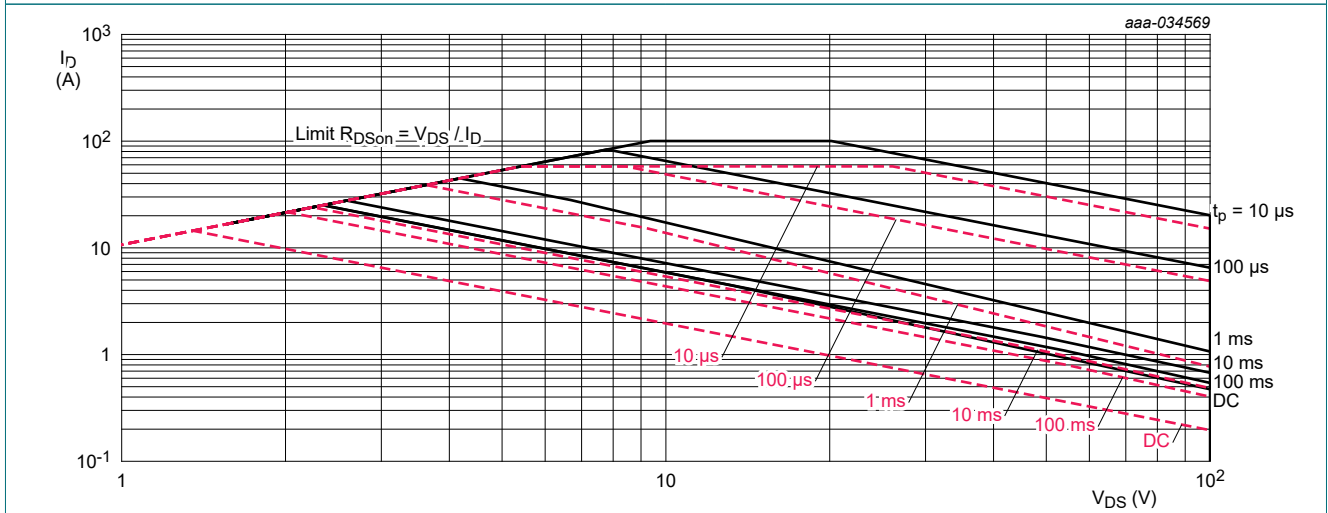


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25 \text{ }^\circ\text{C}$  (solid black line);  $T_{mb} = 125 \text{ }^\circ\text{C}$  (red dashed line);  $I_{DM}$  is a single pulse

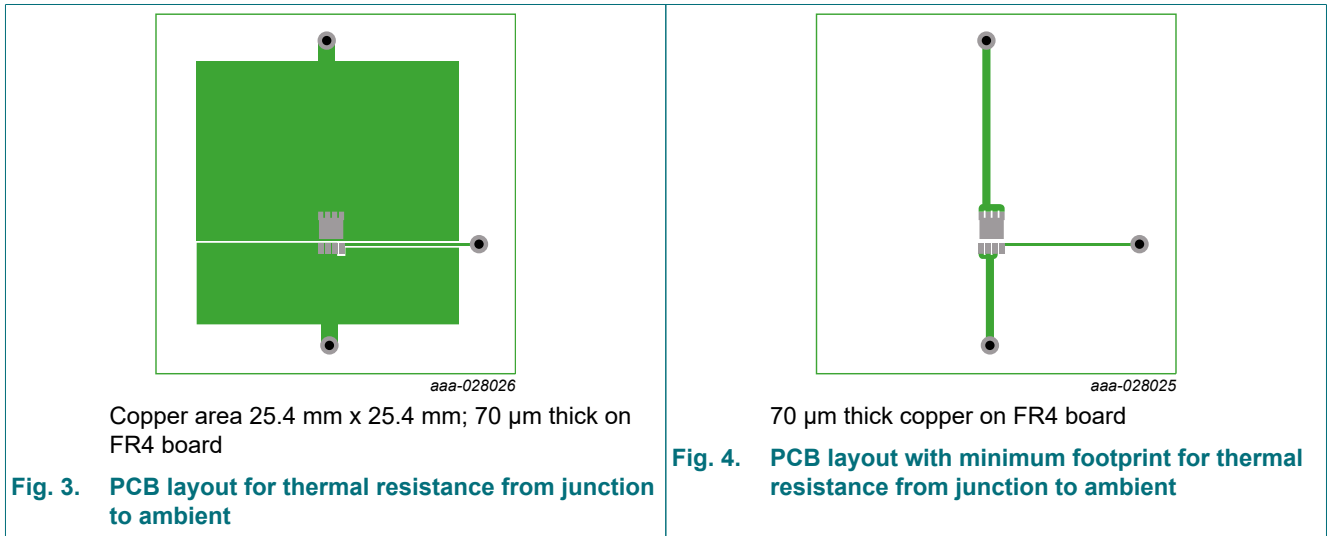
Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

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## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base		-	2.33	2.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 3	-	50	-	K/W
		Fig. 4	-	130	-	K/W



## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	100	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$	2	2.8	3.6	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 175 \text{ }^\circ C$	-	[tbd]	-	V
		$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = -55 \text{ }^\circ C$	-	[tbd]	-	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	[tbd]	-	mV/K
$I_{DSS}$	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	0.003	-	1	μA
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	-	100	μA
$I_{GSS}$	gate leakage current	$V_{DS} = 20 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
		$V_{DS} = -20 \text{ V}; T_j = 25 \text{ }^\circ C$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ C$	-	32	42	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ }^\circ C$	-	50	67	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 175 \text{ }^\circ C$	-	72	95	mΩ
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$	[tbd]	1.3	[tbd]	Ω

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Dynamic characteristics</b>						
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; T <sub>J</sub> = 25 °C	[tbd]	10.5	[tbd]	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	4.6	-	nC
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 10 V; T <sub>J</sub> = 25 °C	[tbd]	4.5	[tbd]	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	2.2	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2.3	-	nC
Q <sub>GD</sub>	gate-drain charge		[tbd]	2	[tbd]	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 50 V; T <sub>J</sub> = 25 °C	-	[tbd]	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 50 V; V <sub>GS</sub> = 0 V; f = 1 MHz; T <sub>J</sub> = 25 °C	[tbd]	612	[tbd]	pF
C <sub>oss</sub>	output capacitance		[tbd]	134	[tbd]	pF
C <sub>rss</sub>	reverse transfer capacitance		[tbd]	4.2	[tbd]	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 50 V; R <sub>L</sub> = 2 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω; T <sub>J</sub> = 25 °C	-	2.2	-	ns
t <sub>r</sub>	rise time		-	1.9	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	5.3	-	ns
t <sub>f</sub>	fall time		-	2.7	-	ns
<b>Source-drain diode</b>						
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>J</sub> = 25 °C	-	-	1	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; Fig. 5	-	31	-	ns
Q <sub>r</sub>	recovered charge	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; T <sub>J</sub> = 25 °C; Fig. 5	-	22	-	nC

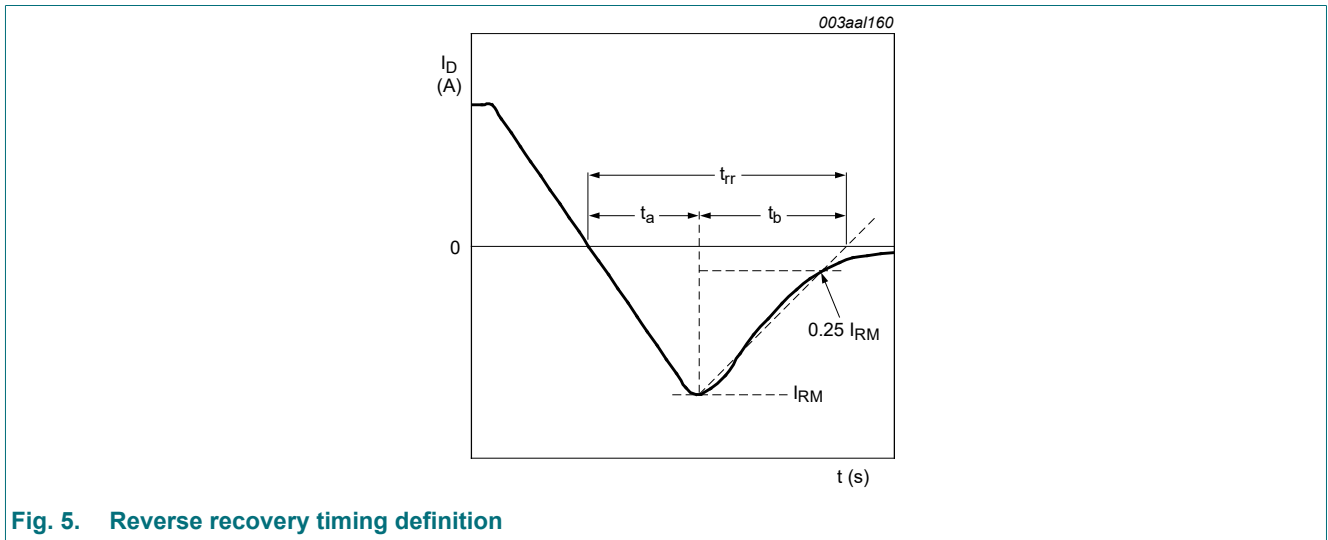


Fig. 5. Reverse recovery timing definition

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### 10. Package outline

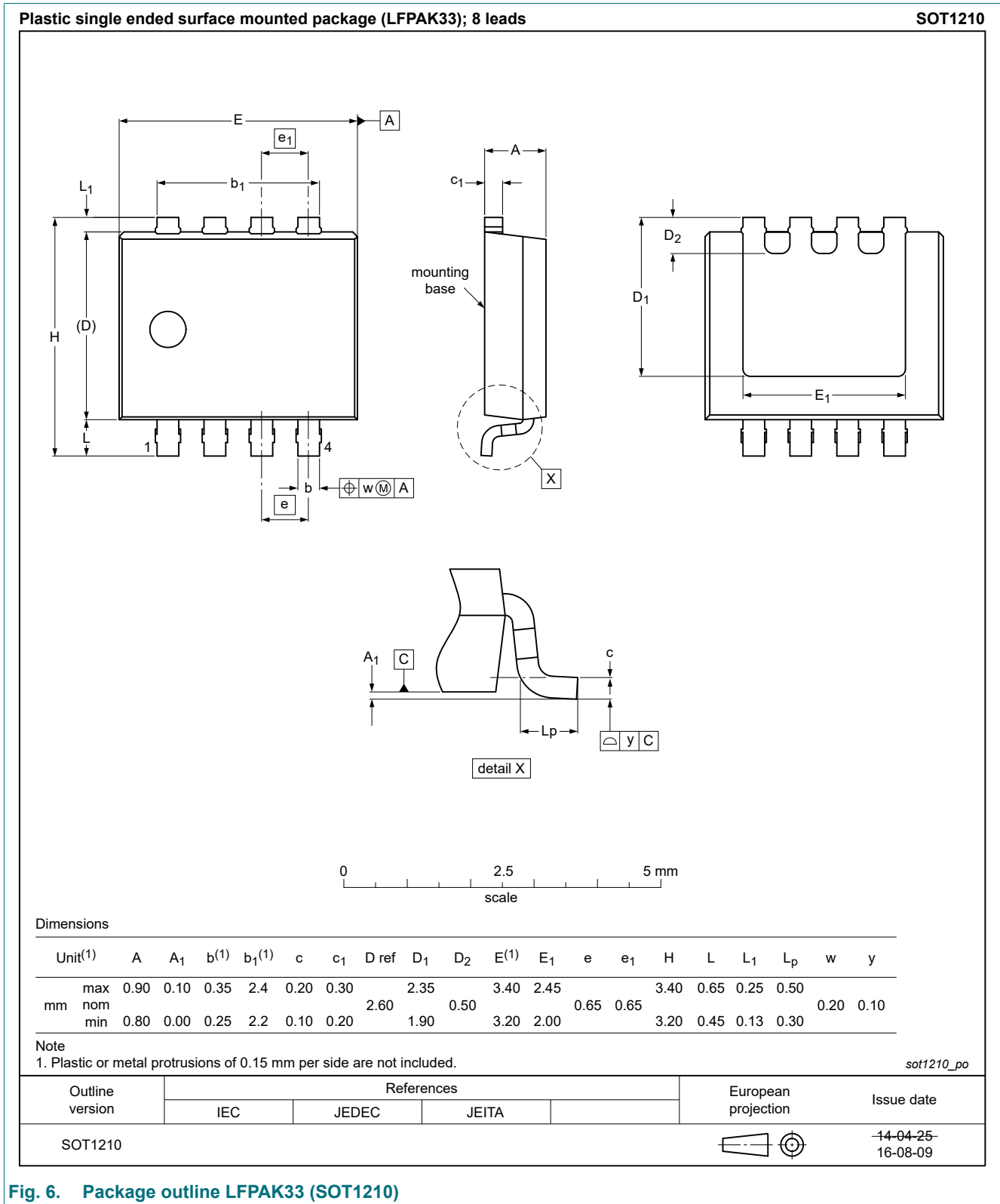
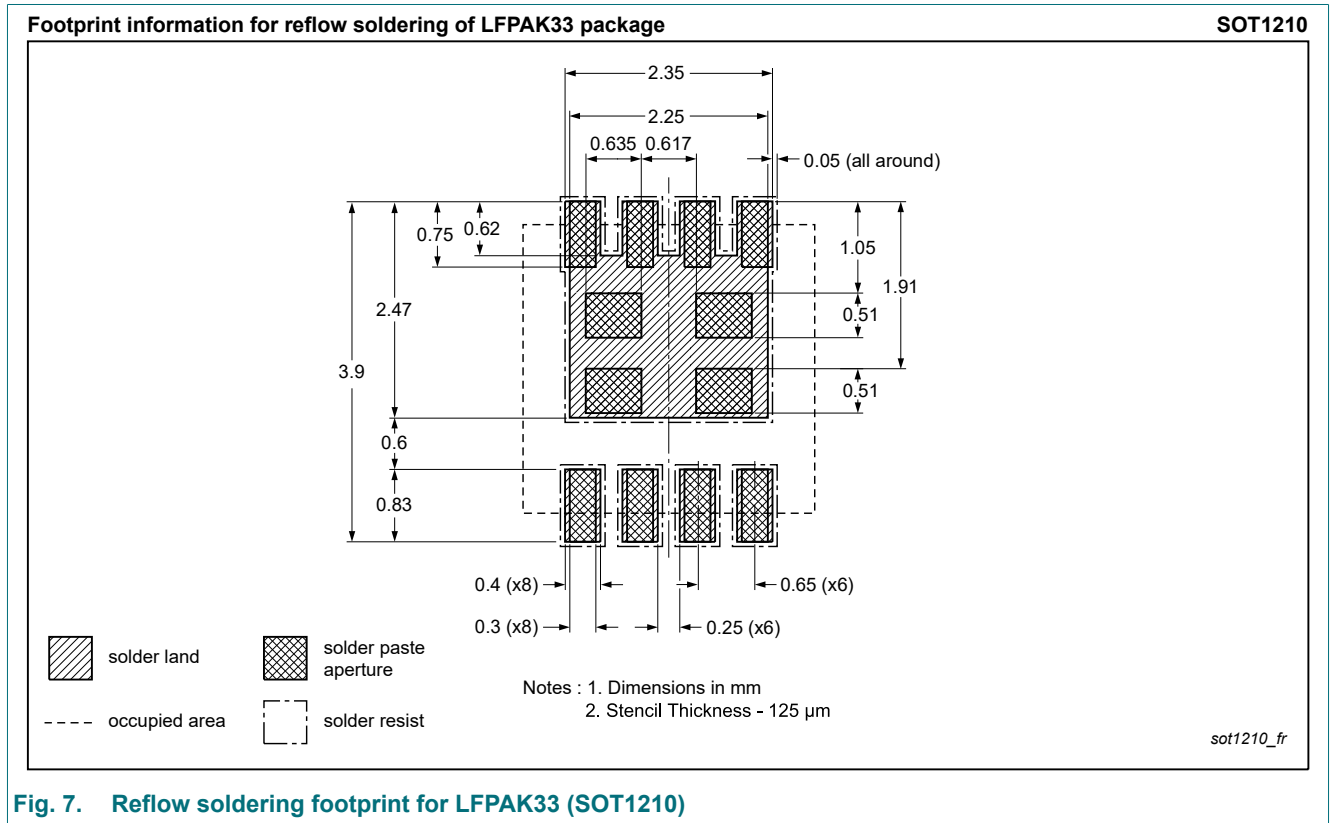


Fig. 6. Package outline LPAK33 (SOT1210)

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## 11. Soldering



## N-channel 100 V 42 mOhm standard level ASFET with enhanced SOA in LPAK33 package. Designed specifically for high power PoE applications

## 12. Legal information

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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